# **30V N-CHANNEL ENHANCEMENT MODE MOSFET**

## SUMMARY

 $V_{(BR)DSS}$ =30V;  $R_{DS(ON)}$ =0.025 $\Omega$  I<sub>D</sub>=6.7A

#### DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

#### **FEATURES**

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

#### **APPLICATIONS**

- DC DC Converters
- Power Management Functions
- Disconnect switches
- Motor control

### **ORDERING INFORMATION**

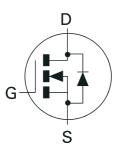
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN3A02X8TA	7″	12mm	1000 units
ZXMN3A02X8TC	13″	12mm	4000 units

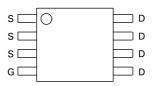
#### **DEVICE MARKING**

• ZXMN

3A02

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### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current V <sub>GS</sub> =10V; T <sub>A</sub> =25°C (b) V <sub>GS</sub> =10V; T <sub>A</sub> =70°C (b) V <sub>GS</sub> =10V; T <sub>A</sub> =25°C (a)	ID	6.7 5.4 5.3	A
Pulsed Drain Current (c)	IDM	24	А
Continuous Source Current (Body Diode) (b)	IS	3.2	А
Pulsed Source Current (Body Diode) (c)	ISM	24	А
Power Dissipation at T <sub>A</sub> =25°C (a) Linear Derating Factor	PD	1.1 8.8	W mW/°C
Power Dissipation at T <sub>A</sub> =25°C (b) Linear Derating Factor	PD	1.8 14.4	W mW/°C
Operating and Storage Temperature Range	Tj:Tstg	-55 to +150	°C

### THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	R <sub>0</sub> JA	113	°C/W
Junction to Ambient (b)	R <sub>0JA</sub>	70	°C/W

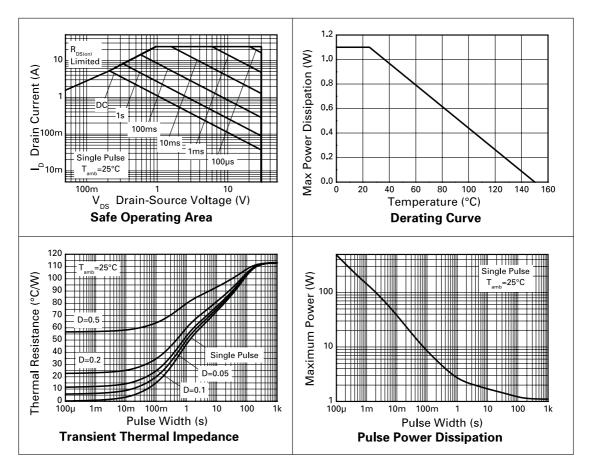
## NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width  $10\mu s$  - pulse width limited by maximum junction temperature.



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### **CHARACTERISTICS**

\* For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

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PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
STATIC	1	1			1	1	
Drain-Source Breakdown Voltage	V(BR)DSS	30			V	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	
Zero Gate Voltage Drain Current	IDSS			1	μA	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	
Gate-Body Leakage	IGSS			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Gate-Source Threshold Voltage	VGS(th)	1			V	I <sub>D</sub> =250μA, V <sub>DS</sub> = V <sub>GS</sub>	
Static Drain-Source On-State Resistance (1)	R <sub>DS(on)</sub>			0.025 0.035	Ω Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =12A V <sub>GS</sub> =4.5V, I <sub>D</sub> =10.2A	
Forward Transconductance (1)(3)	9fs		22		S	V <sub>DS</sub> =10V,I <sub>D</sub> =12A	
DYNAMIC (3)							
Input Capacitance	C <sub>iss</sub>		1400		pF	V <sub>DS</sub> =25 V, V <sub>GS</sub> =0V, f=1MHz	
Output Capacitance	C <sub>oss</sub>		209		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		120		pF		
SWITCHING(2) (3)							
Turn-On Delay Time	<sup>t</sup> d(on)		3.9		ns		
Rise Time	tr		5.5		ns	V <sub>DD</sub> =15V, I <sub>D</sub> =5.5A	
Turn-Off Delay Time	<sup>t</sup> d(off)		35.0		ns	$R_{G}=6.2\Omega$ , $V_{G}S=10V$ (refer to test circuit)	
Fall Time	t <sub>f</sub>		7.6		ns		
Gate Charge	٥ <sub>g</sub>		14.5		nC	V <sub>DS</sub> =15V,V <sub>GS</sub> =5V, I <sub>D=5.5A</sub> (refer to test circuit)	
Total Gate Charge	٥ <sub>g</sub>		26.8		nC		
Gate-Source Charge	Q <sub>gs</sub>		4.7		nC	V <sub>DS</sub> =15V,V <sub>GS</sub> =10V, I <sub>D</sub> =5.5A	
Gate-Drain Charge	Q <sub>gd</sub>		4.7		nC	(refer to test circuit)	
SOURCE-DRAIN DIODE							
Diode Forward Voltage (1)	V <sub>SD</sub>			0.95	V	TJ=25°C, IS=9A, VGS=0V	
Reverse Recovery Time (3)	t <sub>rr</sub>		17		ns	TJ=25°C, IF=5.5A,	
Reverse Recovery Charge (3)	Q <sub>rr</sub>		8.3		nC	di/dt= 100A/µs	

NOTES

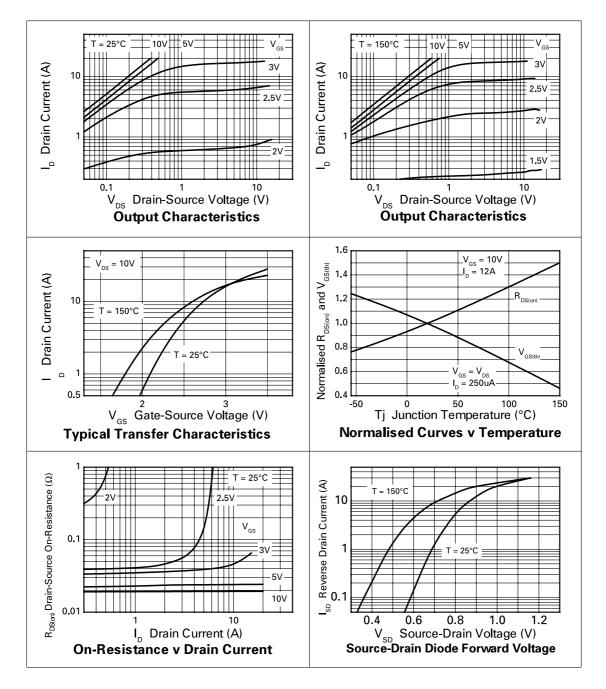
(1) Measured under pulsed conditions. Width=300 $\mu s.$  Duty cycle  $\leq 2\%$ . (2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.



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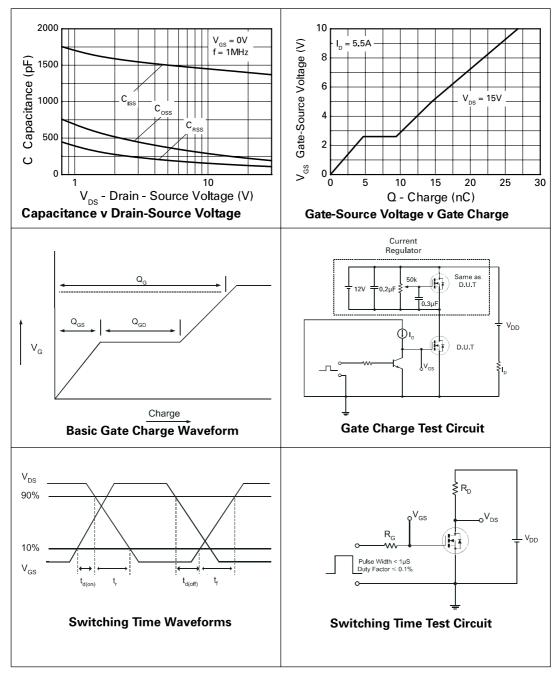
Downloaded From Oneyac.com



### **CHARACTERISTICS**

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ZETEX



### CHARACTERISTICS



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MIN

0.002

0.010

0.005

0.114

0.0256

0.114

0.193

0.016

0°

Inches

MAX

0.043

0.006

0.016

0.009

0.122

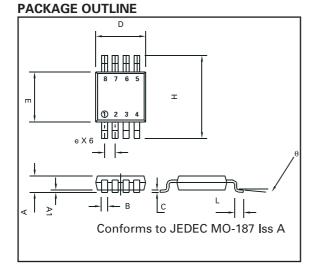
BSC

0.122

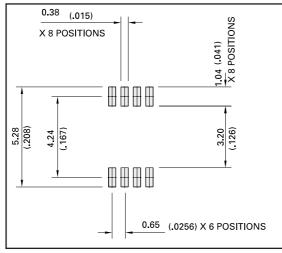
BSC

0.028

6°



### PAD LAYOUT



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PACKA	GE	DIN	1EN!	SION

MIN

0.05

0.25

0.13

2.90

0.65

2.90

4.90

0.40

0°

Millimetres

MAX

1.10

0.15

0.40

0.23

3.10

BSC

3.10

BSC

0.70

6°

DIM

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单击下面可查看定价,库存,交付和生命周期等信息

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